

Today's outline - October 16, 2024





- Diffuse Scattering

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- Modulated structures

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Reading Assignment: Chapter 6.1-6.2

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Reading Assignment: Chapter 6.1-6.2

Homework Assignment #04:

Chapter 4: 2,4,6,7,10

due Friday, October 18, 2024



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- Powder diffraction
- Pair distribution function
- Bragg & Laue geometries

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Homework Assignment #04:

Chapter 4: 2,4,6,7,10

due Friday, October 18, 2024

Homework Assignment #05:

Chapter 5: 1,3,7,9,10

due Monday, October 28, 2024

Truncation rod review



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Truncation rod review

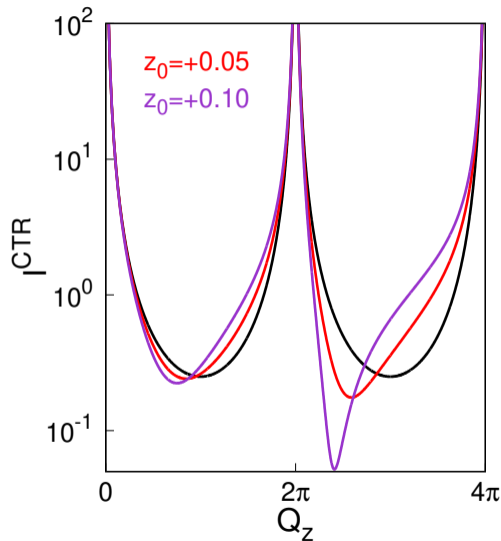


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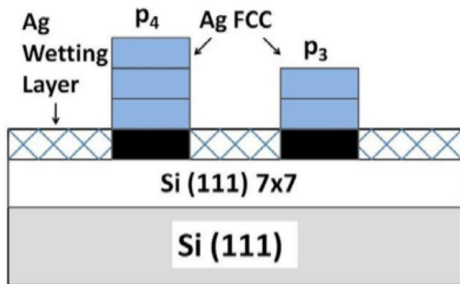
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This effect gets larger for larger momentum transfers

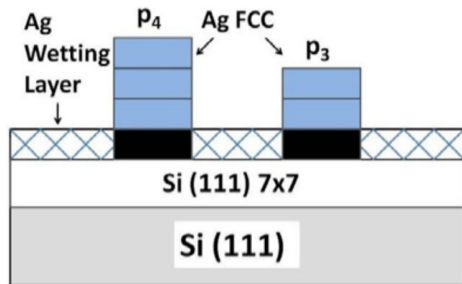


Buried interfaces of Ag films on silicon



"Critical role of a buried interface in the Stranski-Krastanov growth of metallic nanocrystals: Quantum size effects in Ag/Si(111)-(7x7)," Y. Chen et al. *Phys. Rev. Lett.* **114**, 035501 (2015).

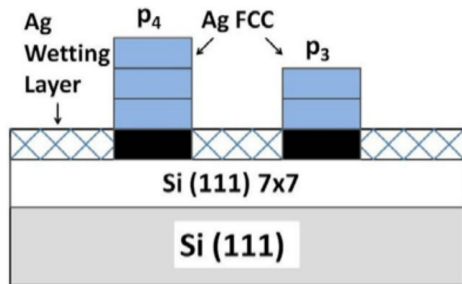
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Understanding the process of surface wetting during thin film deposition is crucial to the semiconductor industry

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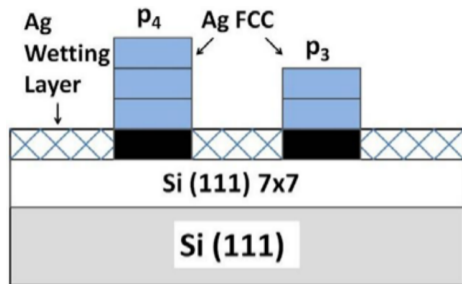


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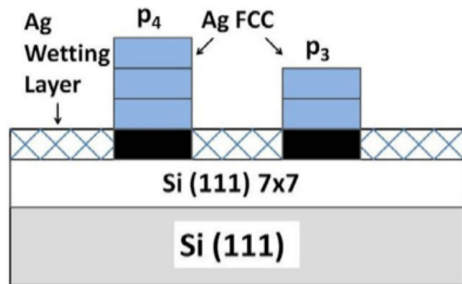
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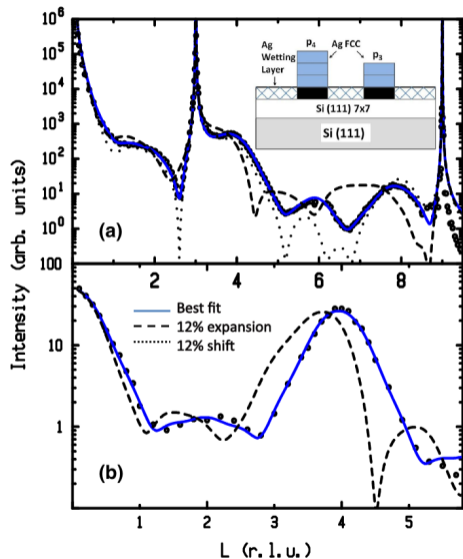
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Ag was thermally evaporated on the surface and both reflectivity measurements of the surface and CTR measurements of the Ag (001) growth layer were performed

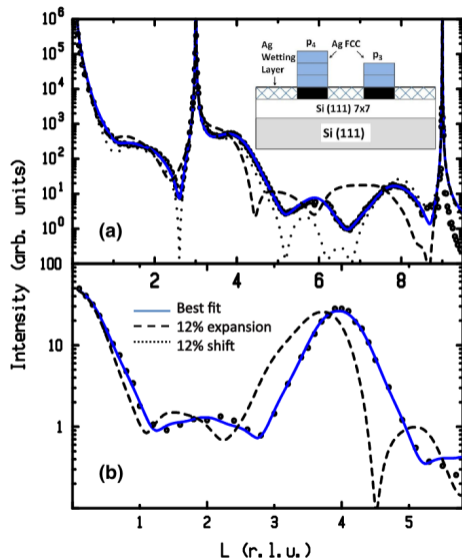
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Reflectivity & CTR measurements



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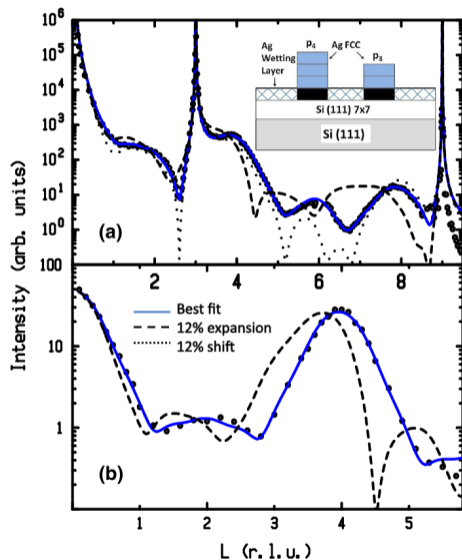
Reflectivity & CTR measurements



Reflectivity “sees” the entire surface while CTR measures only the incommensurate Ag crystalline layer on the surface

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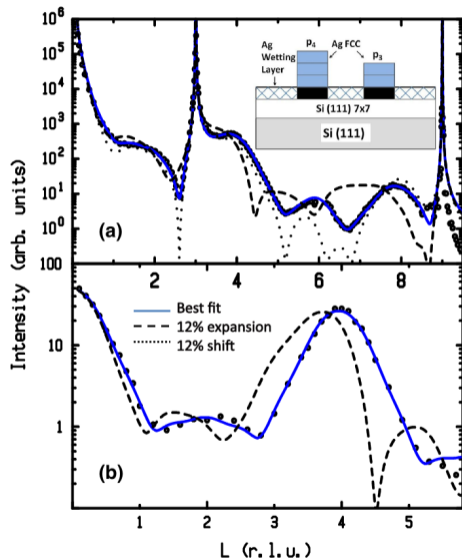


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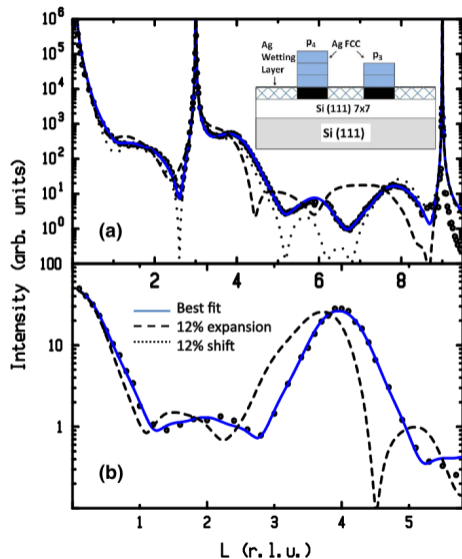
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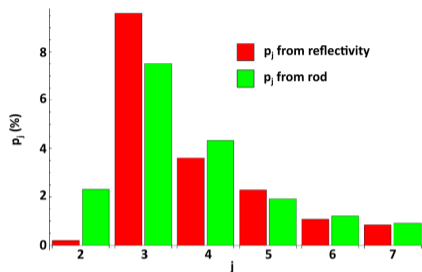
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Modeling shows that the islands are displaced from the surface

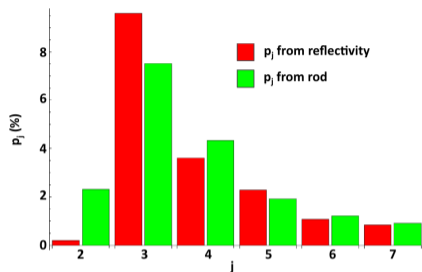
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Ag island height & quantum confinement



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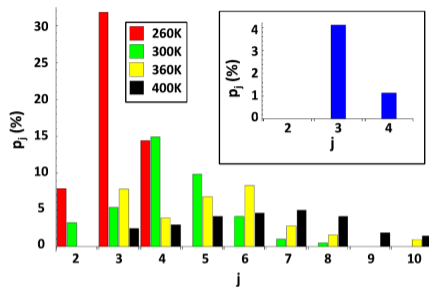
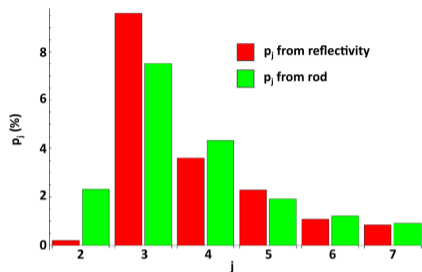
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Island layer height distributions from reflectivity and CTR are well correlated and indicate that 3 layers are the minimum for stability

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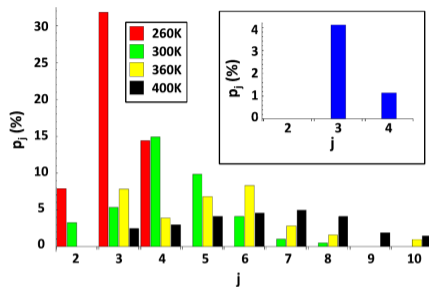
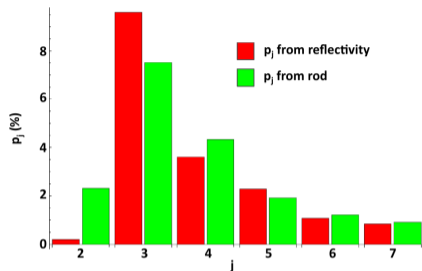
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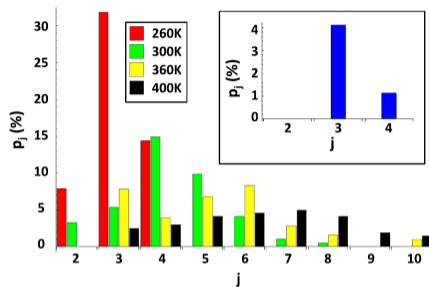
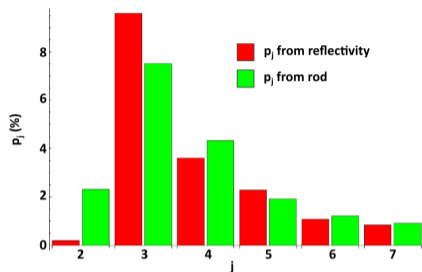


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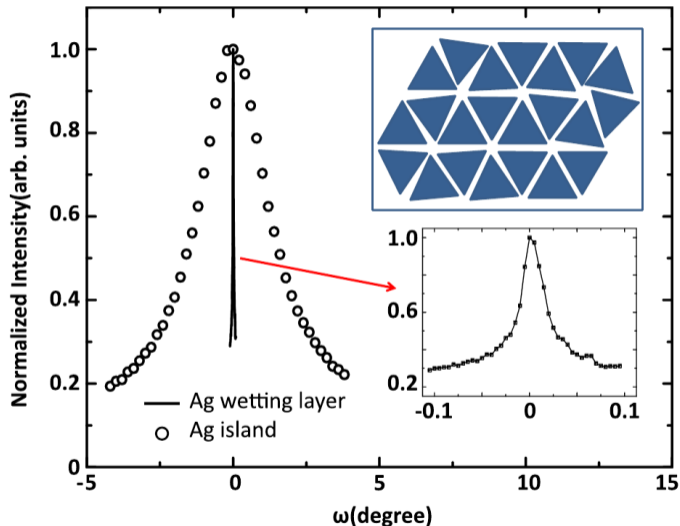
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The exceptional stability of the three layer islands is consistent with quantum confinement effects that drive the growth process

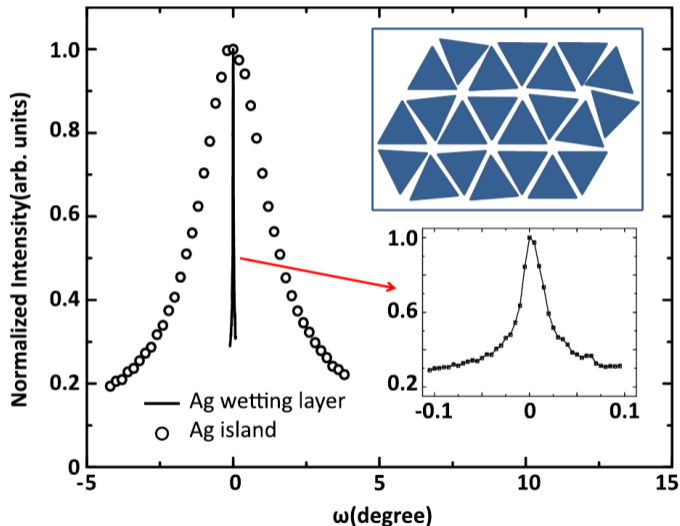
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In plane structure of islands



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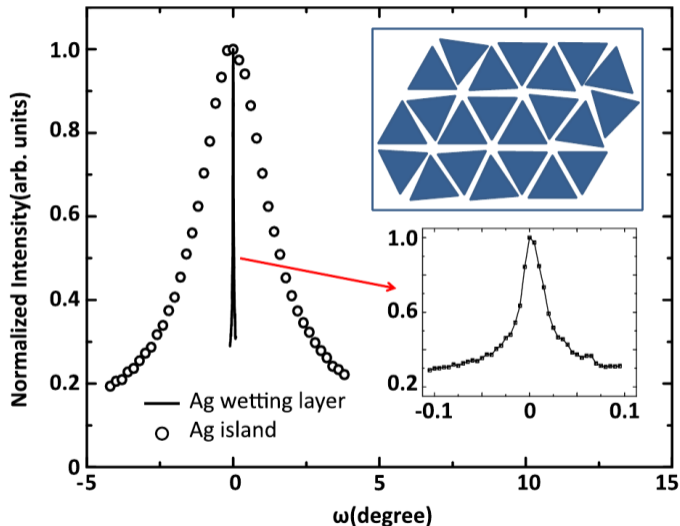
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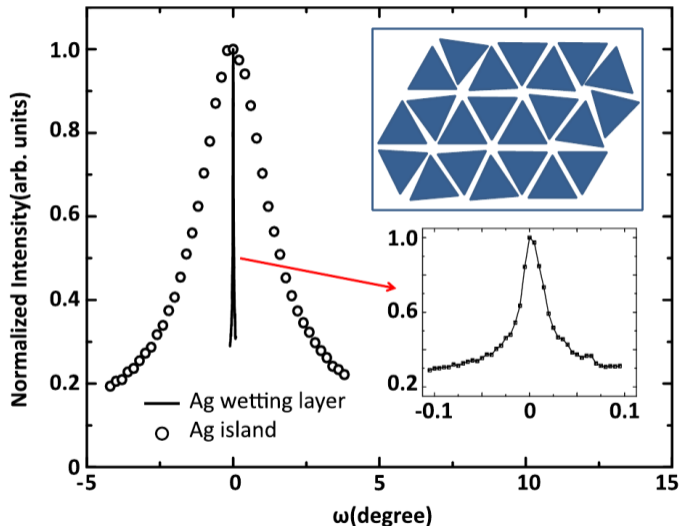
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The large in-plane orientational disorder can be seen from the azimuthal scattering profile that is 3 degrees wide. The narrow peak is the azimuthal scan of the commensurate wetting layer.

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In plane structure of islands



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The islands thus have a weak interaction with the substrate compared to the wetting layer.

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Modulated structures



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However, it is common to see structures where the positions of the atoms is modulated (e.g. charge density waves, magnetic lattices, etc.) according to $x_n = an + u \cos(qan)$, where: a is the lattice parameter, u is the amplitude of the displacement, and $q = 2\pi/\lambda_m$ is the wave vector of the modulation.



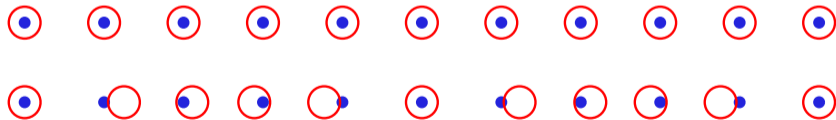
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If λ_m is a multiple or a rational fraction of a , it is called a **commensurate** modulation



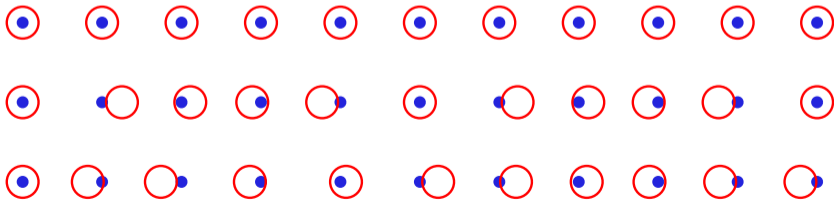
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If λ_m is a multiple or a rational fraction of a , it is called a **commensurate** modulation but if $\lambda_m = ca$, where c is an irrational number, then it is an **incommensurate** modulation.



Diffraction from a modulation



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the diffraction pattern has **main** Bragg peaks plus **satellite** peaks

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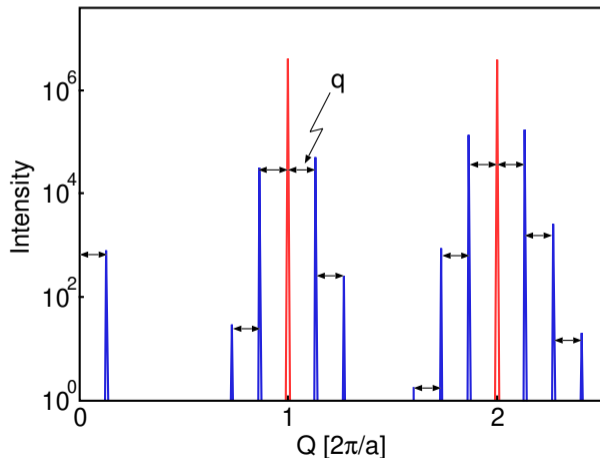


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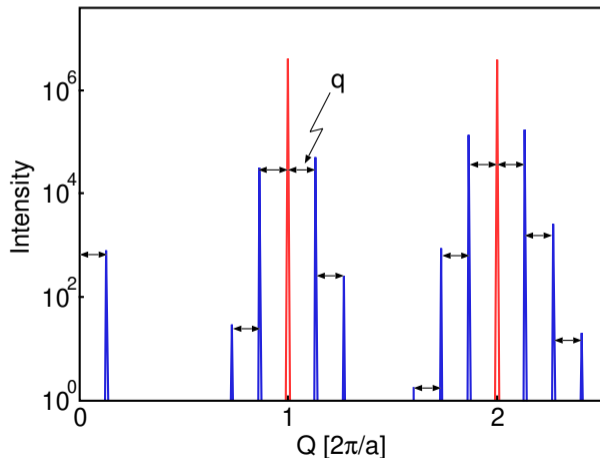


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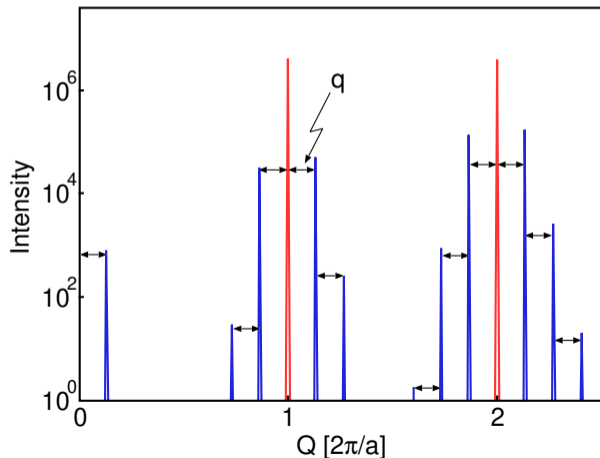
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If the modulation of the structure is a multiple of the lattice parameter, the modulation is simply a superlattice and the actual lattice parameter will be changed.





The only rotational symmetries which permit a space-filling lattice are 2-, 3-, 4-, and 6-fold.



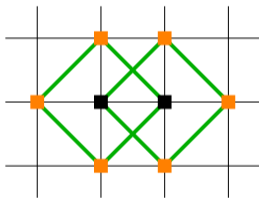
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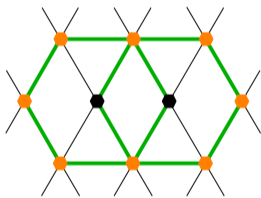
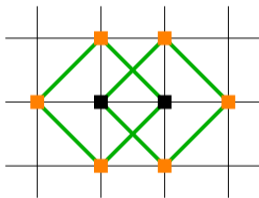


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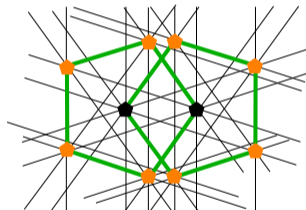
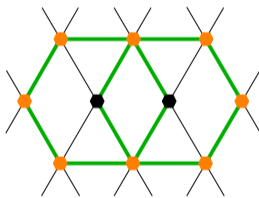
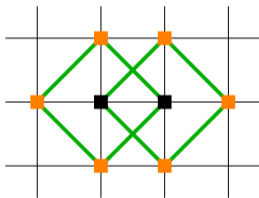


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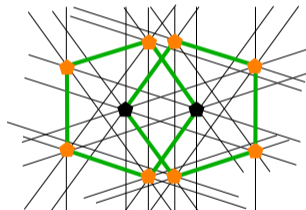
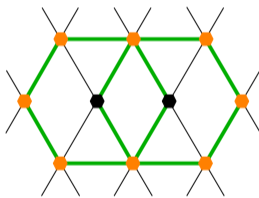
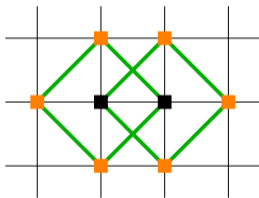


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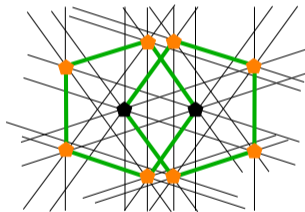
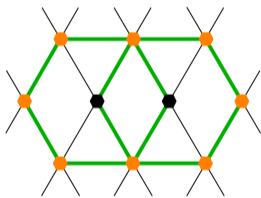
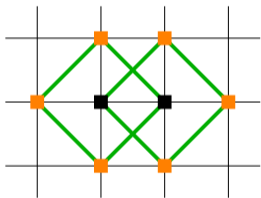


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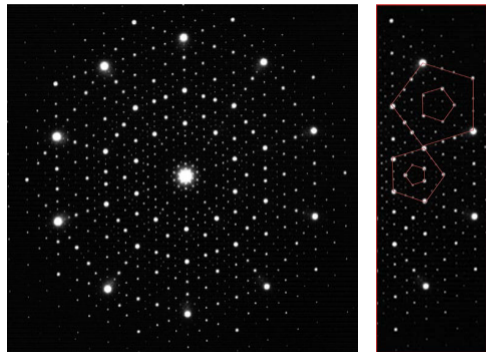
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In 2011 Shechtman was awarded the Nobel Prize in Chemistry

5-fold symmetry



The electron micrographs show that there must be long range order to be able to get such sharp diffraction peaks



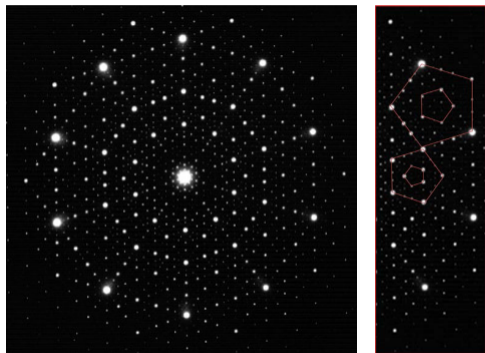
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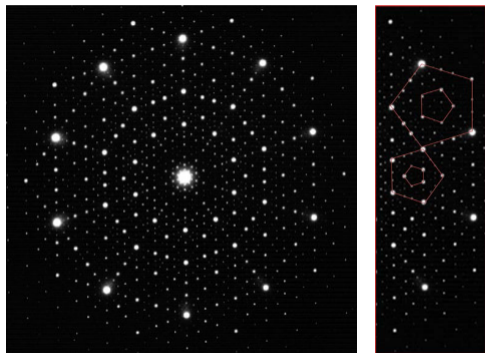
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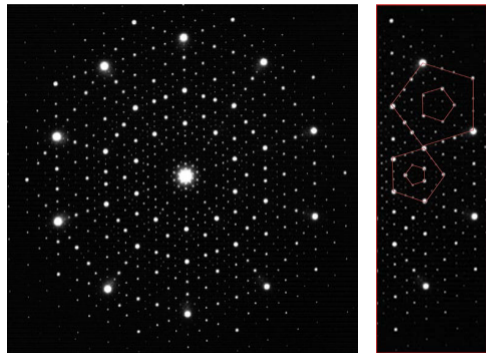
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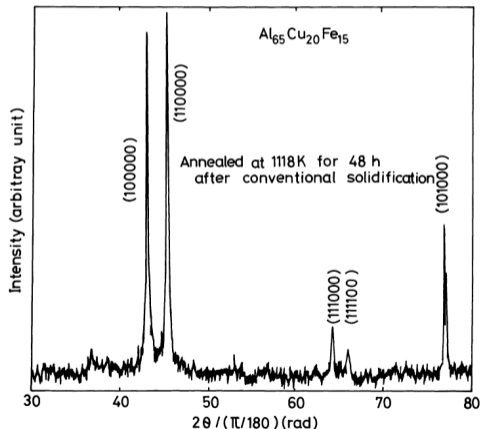
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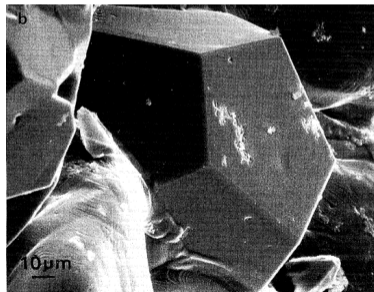
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The second term is the Thermal Diffuse Scattering and actually increases with mean squared displacement.

Thermal Diffuse Scattering



$$I^{TDS} = \sum_m \sum_n f(\vec{Q}) e^{-M} e^{i\vec{Q}\cdot\vec{R}_m} f^*(\vec{Q}) e^{-M} e^{-i\vec{Q}\cdot\vec{R}_n} \left[e^{Q^2 \langle u_{Qm} u_{Qn} \rangle} - 1 \right]$$

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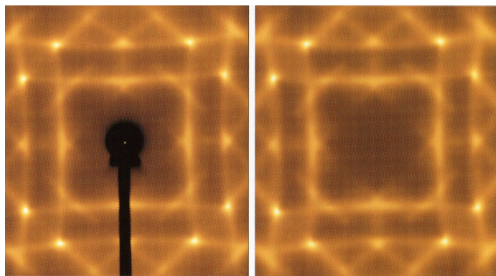


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Thermal Diffuse Scattering

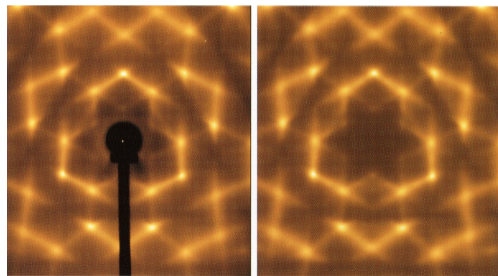


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Thermal Diffuse Scattering

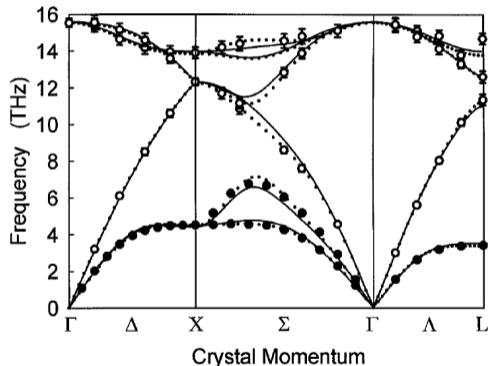


$$I^{TDS} = \sum_m \sum_n f(\vec{Q}) e^{-M} e^{i\vec{Q}\cdot\vec{R}_m} f^*(\vec{Q}) e^{-M} e^{-i\vec{Q}\cdot\vec{R}_n} \left[e^{Q^2 \langle u_{Qm} u_{Qn} \rangle} - 1 \right]$$

The TDS has a width determined by the **correlated displacement of atoms** which is much broader than a Bragg peak.

These correlated motions are just phonons.

A 0.5mm Si wafer illuminated by 28keV x-rays from an APS undulator were used to measure the phonon dispersion curves of silicon



dotted line from this measurement

"Determination of phonon dispersions from x-ray transmission scattering: The example of silicon," M. Holt, et al. *Phys. Rev. Lett.* **83**, 3317 (1999).

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For crystals with several different types of atoms, we generalize the unit cell scattering factor.

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In general, Debye-Waller factors can be anisotropic



The Debye Model

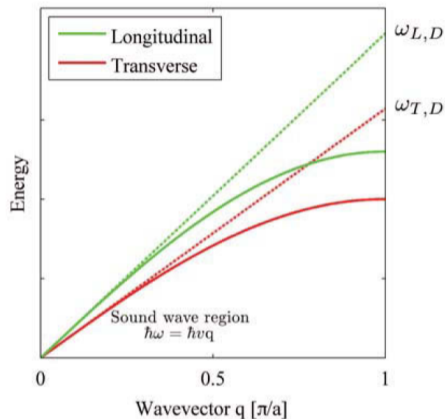
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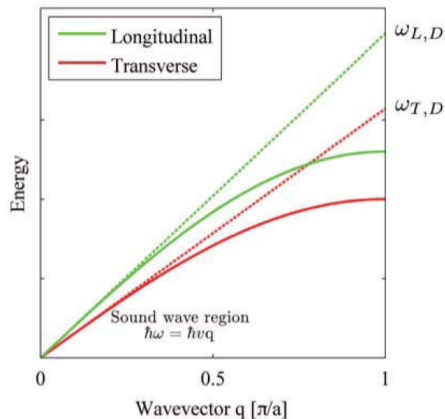
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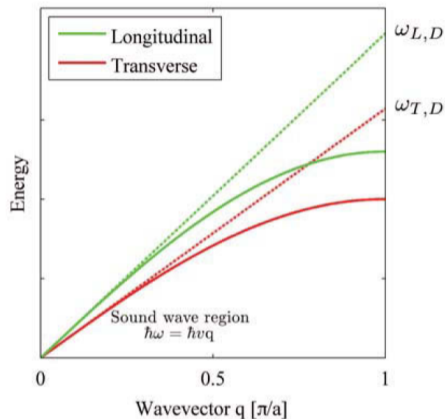
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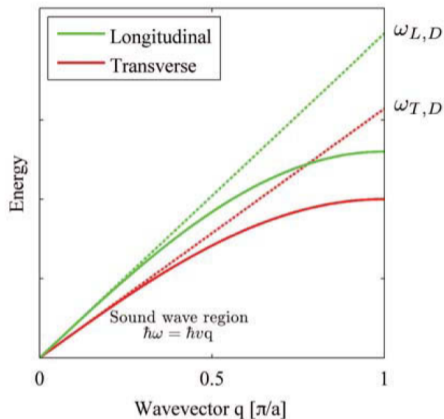


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Debye Temperatures



	A	Θ (K)	$B_{4.2}$	B_{77} (\AA^2)	B_{293}
C*	12	2230	0.11	0.11	0.12
Al	27	428	0.25	0.30	0.72
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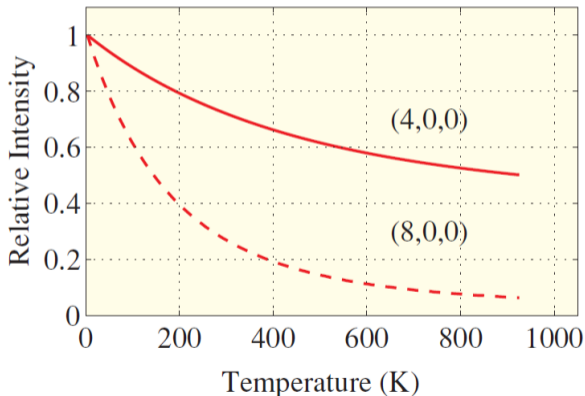
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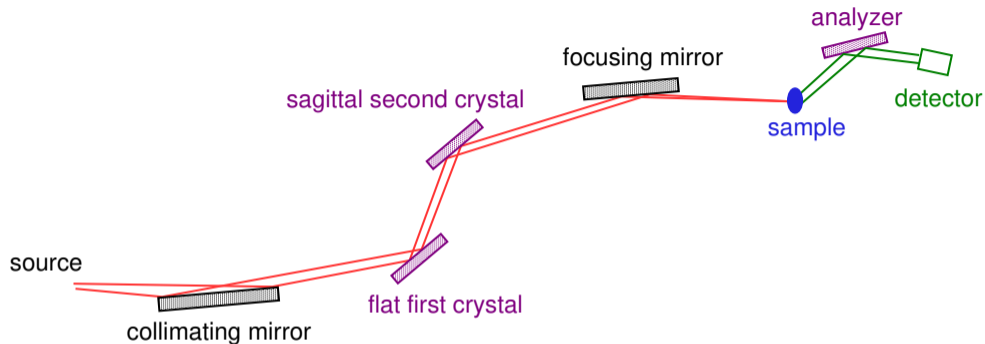
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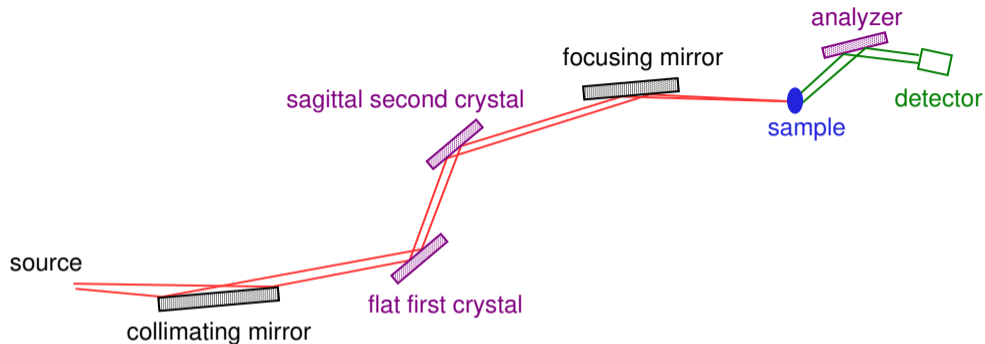


Beamline 11BM at the APS



"A dedicated powder diffraction beamline at the Advanced Photon Source: Commissioning and early operational results," J. Wang et al. *Rev. Sci. Instrum.* **79**, 085105 (2008).

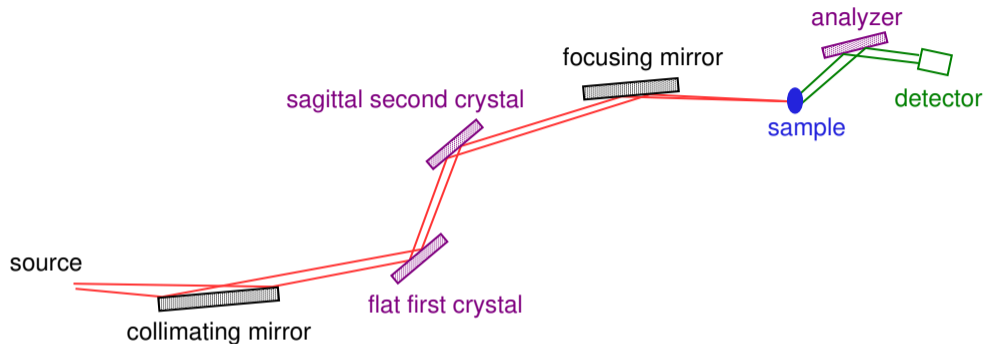
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2D detectors have limited angular resolution, for high resolution routine powder diffraction, beamlines such as 11BM are ideal

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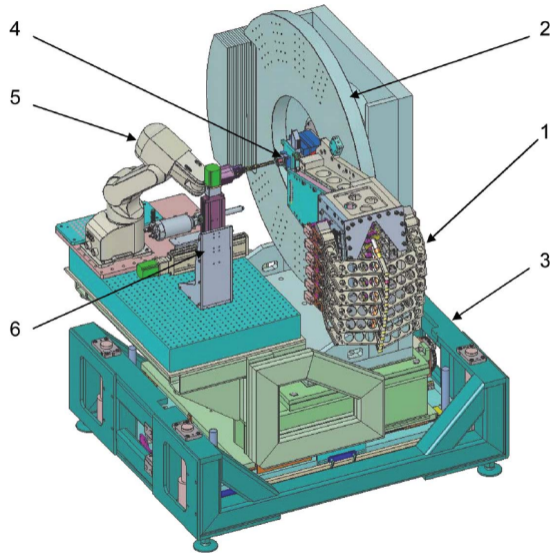


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The initial collimating mirror makes the beam more parallel and then it is focused horizontally and vertically to the sample

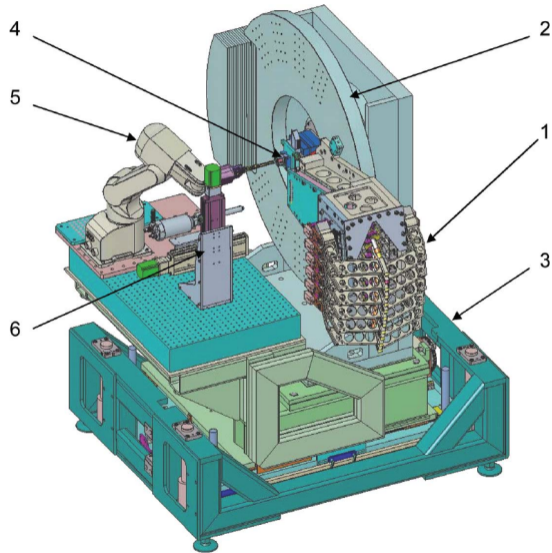
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The high resolution analyzer



"A twelve-analyzer detector system for high resolution powder diffraction," P.L. Lee et al. *J. Synch. Rad.* **15**, 427-432

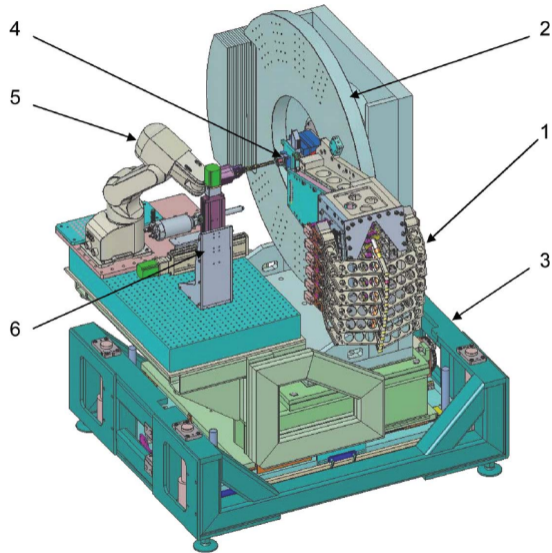
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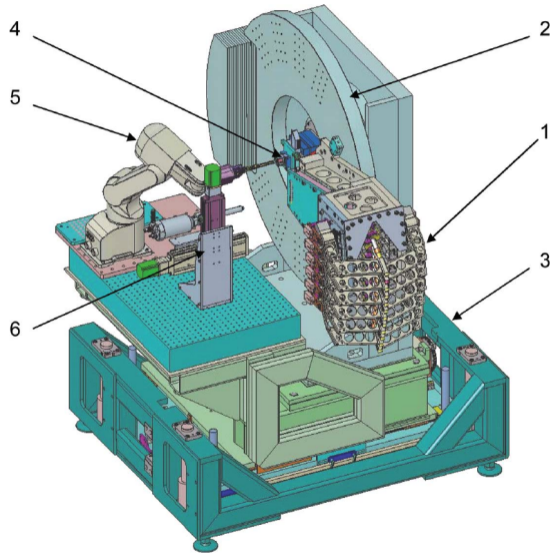


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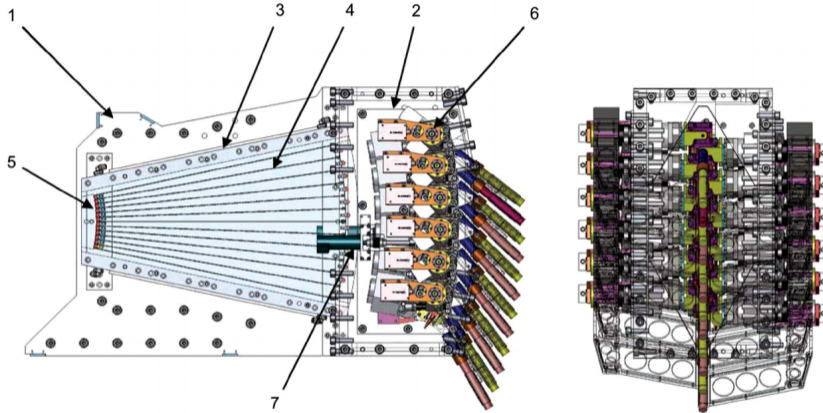
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High resolution is achieved with a 12 crystal analyzer system which is rotated on the main circle of the goniometer

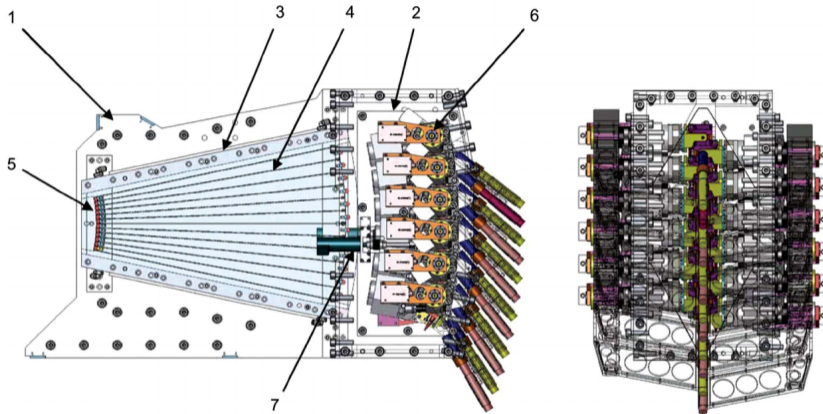
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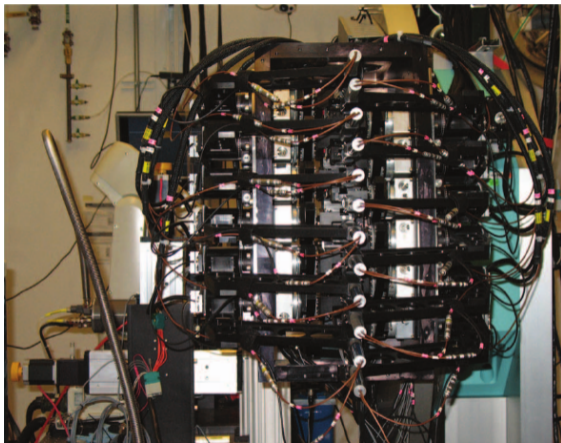
The high resolution analyzer



Each of the 12 analyzer crystals is tuned to the desired scattering energy and as the entire assembly is scanned, all twelve banks are collecting data and then are merged

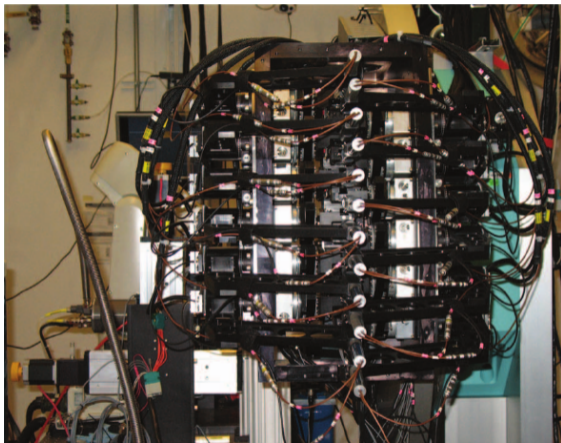
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The analyzer and robot arm

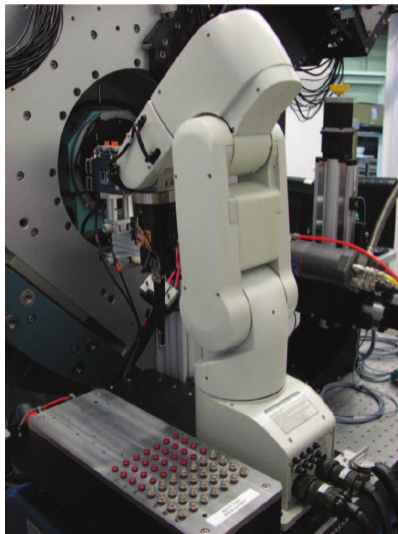


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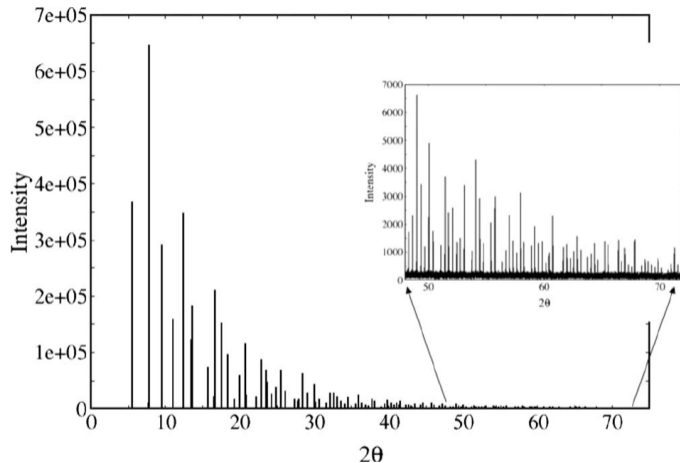


Samples are in Kapton capillaries and magnetic bases for remote mounting



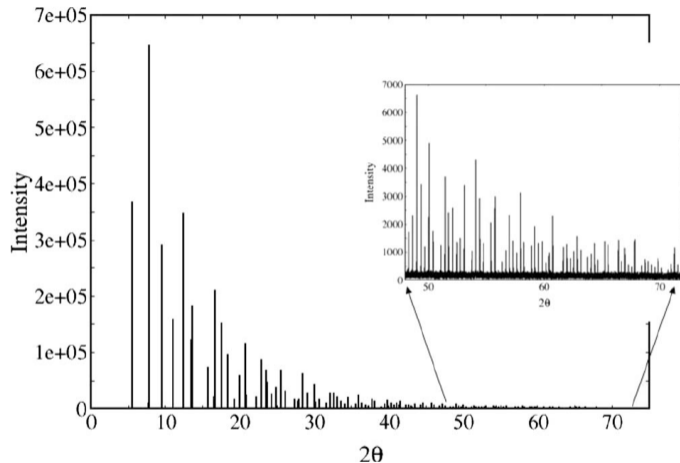
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Data from high resolution LaB₆ standard



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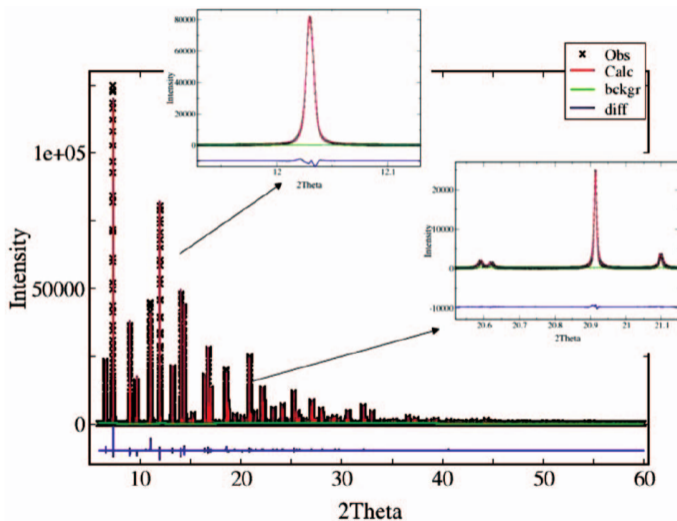
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High resolution data with high count rates can be obtained out to very high angles with a wavelength of $\lambda \approx 0.5\text{\AA}$.

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Refinement of SiO_2 and Al_2O_3



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